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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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24122	7590	05/12/2005	EXAMINER	
THORP REED & ARMSTRONG, LLP ONE OXFORD CENTRE 301 GRANT STREET, 14TH FLOOR PITTSBURGH, PA 15219-1425			ELMORE, REBA I	
		ART UNIT	PAPER NUMBER	
		2187		

DATE MAILED: 05/12/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	Application No.	Applicant(s)
	10/016,799	HANG, CHIA-LUN
	Examiner	Art Unit
	Reba I. Elmore	2187

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

1) Responsive to communication(s) filed on 23 March 2005.  
 2a) This action is **FINAL**.      2b) This action is non-final.  
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

4) Claim(s) 1-58 is/are pending in the application.  
 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.  
 5) Claim(s) \_\_\_\_\_ is/are allowed.  
 6) Claim(s) 1-58 is/are rejected.  
 7) Claim(s) \_\_\_\_\_ is/are objected to.  
 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

9) The specification is objected to by the Examiner.  
 10) The drawing(s) filed on \_\_\_\_\_ is/are: a) accepted or b) objected to by the Examiner.  
     Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
     Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
 a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____	5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)
	6) <input type="checkbox"/> Other: _____

## DETAILED ACTION

1. Claims 1-58 are presented for examination.

### ***DRAWINGS***

2. The objection to the drawings is *withdrawn* due to the amendment.

### ***SPECIFICATION***

3. The specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

### ***35 USC § 102***

4. The rejection of claims 1-58 as being anticipated by Nakamura is *maintained* and repeated below. Additional explanation is given within the body of the art rejection for applying the Nakamura reference, however, neither the reference used nor the legal basis for the rejection have been changed.
5. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

6. Claims 1-58 are rejected under 35 U.S.C. 102(e) as being anticipated by Nakamura.
7. Nakamura teaches the invention (claim 1) as claimed including a combination comprising:

a processor as the processing circuit (e.g., see Figure 1, element 2); and, a transparent memory array comprising a plurality of memory banks, each of the plurality of memory banks being directly connected to the processor, the memory array operable to function without *at least one of* a precharge signal, a row address latch signal and a column address latch signal. The embedded SDRAM teaches the transparent memory array as a memory array which has a refresh operation for maintaining data in a power down mode without input from a programmer or system designer. The refresh operation is performed using a refresh address counter without supplying the address to the address buffer of the memory array for each cell of the array (e.g., see Figures 6-7 and paragraphs 0069-0077).

As to claim 2, Nakamura teaches the processor simultaneously communicates with at least two of the plurality of memory banks (e.g., see paragraphs 0057-0059). The simultaneous reading and writing of data from/to more than one of the plurality of memory banks is taught as part of a power down mode refresh operation which uses a data input buffer connected to a command latch and controller for each memory bank of the memory array. Figure 2 shows connectivity of element 24 (command latch) from element 13 (command decoder) for each memory bank.

As to claim 3, Nakamura teaches one of the memory banks comprises at least one of a row address decoder, a column address decoder and a controller (e.g., see Figure 2).

As to claim 4, Nakamura teaches the processor provides at least one of a row address signal and a column address signal to the plurality of memory banks, the row address signal having a row address latency period being dependent primarily on a row address decoding

pipeline and the column address signal having a column address latency period being dependent primarily on a column address decoding pipeline (e.g., see Figure 2).

As to claim 5, Nakamura teaches on of the plurality of memory banks is a synchronous dynamic random access memory (e.g., see Figure 1 and paragraph 0053).

8. Nakamura teaches the invention (claim 6) as claimed including a combination comprising:

a processor as the processing circuit (e.g., see Figure 1, element 2); and,

a plurality of transparent memory arrays being directly connected to the processor, and each operable to function without *at least one of* a precharge signal, a row address latch signal, and a column address latch signal. The embedded SDRAM teaches the transparent memory array as a memory array which has a refresh operation for maintaining data in a power down mode without input from a programmer or system designer. The refresh operation is performed using a refresh address counter without supplying the address to the address buffer of the memory array for each cell of the array (e.g., see Figures 6-7 and paragraphs 0069-0077).

As to claim 7, Nakamura teaches the processor simultaneously communicates with at least two of the plurality of transparent memory arrays (e.g., see paragraphs 0057-0059). The simultaneous reading and writing of data from/to more than one of the plurality of memory banks is taught as part of a power down mode refresh operation which uses a data input buffer connected to a command latch and controller for each memory bank of the memory array.

Figure 2 shows connectivity of element 24 (command latch) from element 13 (command decoder) for each memory bank.

As to claim 8, Nakamura teaches one of the plurality of transparent memory arrays further comprises at least one of a row address decoder, a column address decoder, a controller and a plurality of individual memory cells (e.g., see Figure 2).

As to claim 9, Nakamura teaches the processor provides at least one of a row address signal and a column address signal to the plurality of memory banks, the row address signal having a row address latency period being dependent primarily on a row address decoding pipeline and the column address signal having a column address latency period being dependent primarily on a column address decoding pipeline (e.g., see Figure 2).

As to claim 5, Nakamura teaches one of the plurality of transparent memory arrays is a synchronous dynamic random access memory (e.g., see Figure 1 and paragraph 0053).

9. Nakamura teaches the invention (claim 11) as claimed including a combination comprising:

an integrated circuit having a processor (e.g., see Figure 1, element 2); and,  
an embedded memory array, the memory array having a plurality of controllers (e.g., see Figure 2, element 26) and a plurality of memory banks, each of the memory banks being independently connected to one of the plurality of controllers, each of the controllers being independently connected to the processor (e.g., see Figure 2 and paragraphs 0056-0061). Figure 2 shows each memory bank of the memory array has a memory controller, element 26.

As to claim 12, Nakamura teaches the memory array further comprises:  
a plurality of row address decoders, each of the row address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2); and,

a plurality of column address decoders, each of the column address decoders being connected to one of the memory banks and to one of the controller (e.g., see Figure 2).

As to claim 13, Nakamura teaches the memory array further comprises a data bus having a plurality of data lines, at least one of the plurality of data lines being connected to each of the memory banks (e.g., see Figure 2).

As to claim 14, Nakamura teaches the data bus is operable to simultaneously receive data from each of the memory banks (e.g., see paragraphs 0057-0059).

As to claim 15, Nakamura teaches the data bus is operable to simultaneously provide data to each of the memory banks (e.g., see paragraphs 0057-0059).

As to claim 16, Nakamura teaches the processor is operable to simultaneously send address information to more than one of the plurality of row address decoders and the plurality of column address decoders (e.g., see paragraphs 0057-0059).

As to claim 17, Nakamura teaches the embedded memory array is comprised of synchronous dynamic random access memory (e.g., see Figure 1 and paragraph 0053).

10. Nakamura teaches the invention (claim 18) as claimed comprising:  
an integrated circuit having a processor (e.g., see Figure 1, element 2); and,  
an embedded memory array, the memory array having a plurality of memory banks, each of the memory banks being independently connected to the processor (e.g., see Figure 2 and paragraphs 0056-0061).

As to claim 19, Nakamura teaches the memory array further comprises:  
a plurality of controllers, each of the plurality of controllers being independently connected to the processor (e.g., see Figure 2);

a plurality of row address decoders, each of the row address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2); and,

a plurality of column address decoders, each of the column address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2).

As to claim 20, Nakamura teaches the memory array has a data bus having a plurality of data lines, at least one of the plurality of data lines being connected to each of the memory banks (e.g., see Figure 2).

As to claim 21, Nakamura teaches the data bus is operable to simultaneously receive data from each of the memory banks (e.g., see paragraphs 0057-0059).

As to claim 22, Nakamura teaches the data bus is operable to simultaneously provide data to each of the memory banks (e.g., see paragraphs 0057-0059).

As to claim 23, Nakamura teaches the processor is operable to simultaneously send address information to more than one of the plurality of controllers (e.g., see paragraphs 0057-0059).

As to claim 24, Nakamura teaches the embedded memory array is comprised of synchronous dynamic random access memory (e.g., see Figure 1 and paragraph 0053).

11. Nakamura teaches the invention (claim 25) as claimed including a combination, comprising:

a processor as the processing circuit (e.g., see Figure 1, element 2); and,

a plurality of transparent SDRAM arrays directly connected to the processor as embedded SDRAM. The embedded SDRAM teaches the transparent memory array as a memory array which has a refresh operation for maintaining data in a power down mode without input from a

programmer or system designer. The refresh operation is performed using a refresh address counter without supplying the address to the address buffer of the memory array for each cell of the array (e.g., see Figures 6-7 and paragraphs 0069-0077).

As to claim 26, Nakamura teaches each of the plurality of transparent SDRAM memory arrays further comprises:

a plurality of memory banks (e.g., see Figure 2);

a plurality of controllers, each of the plurality of controllers being independently connected to the processor and to one of the plurality of memory banks (e.g., see Figure 2);

a plurality of row address decoders, each of the row address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2); and,

a plurality of column address decoders, each of the column address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2).

As to claim 27, Nakamura teaches the memory array has a data bus having a plurality of data lines, at least one of the plurality of data lines being connected to each of the memory banks (e.g., see Figure 2).

As to claim 28, Nakamura teaches the data bus is operable to simultaneously receive data from each of the memory banks (e.g., see Figure 1 and paragraph 0053).

As to claim 29, Nakamura teaches the data bus is operable to simultaneously provide data to each of the memory banks (e.g., see Figure 1 and paragraph 0053).

As to claim 30, Nakamura teaches the processor is operable to simultaneously send address information to more than one of the plurality of controllers (e.g., see Figure 1 and paragraph 0053).

12. Nakamura teaches the invention (claim 31) as claimed including a combination comprising:

a processor as the processing circuit (e.g., see Figure 1, element 2); and,

a transparent SDRAM having a plurality of memory banks, each of the plurality of memory banks being directly connected to the processor as embedded SDRAM. The embedded SDRAM teaches the transparent memory array as a memory array which has a refresh operation for maintaining data in a power down mode without input from a programmer or system designer. The refresh operation is performed using a refresh address counter without supplying the address to the address buffer of the memory array for each cell of the array (e.g., see Figures 6-7 and paragraphs 0069-0077).

As to claim 32, Nakamura teaches each of the plurality of transparent SRAM memory arrays further comprises:

a plurality of controllers, each of the plurality of controllers being independently connected to the processor and to one of the plurality of memory banks (e.g., see Figure 2);

a plurality of row address decoders, each of the row address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2); and,

a plurality of column address decoders, each of the column address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2).

As to claim 33, Nakamura teaches the memory array has a data bus having a plurality of data lines, at least one of the plurality of data lines being connected to each of the memory banks (e.g., see Figure 2).

As to claim 34, Nakamura teaches the data bus is operable to simultaneously receive data from each of the memory banks (e.g., see Figure 1 and paragraph 0053).

As to claim 35, Nakamura teaches the data bus is operable to simultaneously provide data to each of the memory banks (e.g., see Figure 1 and paragraph 0053).

As to claim 36, Nakamura teaches the processor is operable to simultaneously send address information to more than one of the plurality of controllers (e.g., see Figure 1 and paragraph 0053).

13. Nakamura teaches the invention (claim 37) as claimed including a combination comprising:

a processor as the processing circuit (e.g., see Figure 1, element 2); and,  
a transparent SDRAM having a plurality of memory banks connected to the processor such that the processor may simultaneously access more than one of the plurality of memory banks as embedded SDRAM (e.g., see Figures 1-2 and paragraphs 0053-0060). Figure 2 shows each memory bank of the SDRAM has a command latch circuit for supplying the commands to the banks of the array. A refresh command is sent to each individual controller for each memory bank (e.g., see paragraph 0057 and Figure 2).

As to claim 38, Nakamura teaches each of the plurality of transparent SDRAM memory arrays further comprises:

a plurality of controllers, each of the plurality of controllers being independently connected to the processor and to one of the plurality of memory banks (e.g., see Figure 2);  
a plurality of row address decoders, each of the row address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2); and,

a plurality of column address decoders, each of the column address decoders being connected to one of the memory banks and to one of the controllers (e.g., see Figure 2).

As to claim 39, Nakamura teaches the memory array has a data bus having a plurality of data lines, at least one of the plurality of data lines being connected to each of the memory banks (e.g., see Figure 2).

As to claim 40, Nakamura teaches the data bus is operable to simultaneously receive data from each of the memory banks (e.g., see Figure 1 and paragraph 0053).

As to claim 41, Nakamura teaches the data bus is operable to simultaneously provide data to each of the memory banks (e.g., see Figure 1 and paragraph 0053).

As to claim 42, Nakamura teaches the processor is operable to simultaneously send address information to more than one of the plurality of controllers (e.g., see Figure 1 and paragraph 0053).

14. Nakamura teaches the invention (claim 43) as claimed including a transparent memory array comprising:

a plurality of memory banks each comprised of a plurality of memory cells (e.g., see Figure 2); and,

a plurality of peripheral devices for writing information into and reading information out of the memory cells, the plurality of peripheral devices including a plurality of controllers (e.g., see Figure 2, element 26), one of each the plurality of controllers connected to one of each of the plurality of memory banks and wherein the plurality of controllers is operable to simultaneously communicate with a processor (e.g., see Figure 2 and paragraphs 0056-0060). Figure 2 shows

each memory bank of the SDRAM has a command latch circuit for supplying the commands to each of the banks of the array.

As to claim 44, Nakamura teaches the plurality of peripheral devices further comprises: a plurality of row address decoders, each of the plurality of row address decoders having a row address input bus and a row address output bus, at least one of the plurality of row address decoders having the row address input bus connected to one of the plurality of controllers and having the row address output bus connected to one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060); and,

a plurality of column address decoders, each of the plurality of column address decoders having a column address input bus and a column address output bus at least one of the plurality of column address decoders having the column address input bus connected to at least one of the plurality of controllers and having the column address output bus connected to at least one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 45, Nakamura teaches the plurality of controllers are operable to simultaneously exchange at least one of the address information and data with a processor (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 46, Nakamura teaches the plurality of controllers are operable to simultaneously exchange at least one of the address information and data with the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 47, Nakamura teaches a data bus, the data bus having a plurality of data lines connected with each of the plurality of memory banks, the data bus operable to simultaneously

carry data signals from each of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 48, Nakamura teaches at least two of the memory arrays have a different data signal burst mode (e.g., see Figure 2 and paragraphs 0056-0060).

15. Nakamura teaches the invention (claim 49) as claimed including a method for decreasing the access latency of an integrated circuit having a processor and a plurality of embedded memory arrays having a plurality of memory banks, the method comprising:

connecting each of the plurality of memory banks to the processor (e.g., see Figure 2 and paragraphs 0056-0060); and,

simultaneously accessing at least two of the plurality of embedded memory banks with the processor (e.g., see Figure 2 and paragraphs 0056-0060). The embedded SDRAM teaches the transparent memory array as a memory array which has a refresh operation for maintaining data in a power down mode without input from a programmer or system designer. The refresh operation is performed using a refresh address counter without supplying the address to the address buffer of the memory array for each cell of the array (e.g., see Figures 6-7 and paragraphs 0069-0077).

As to claim 50, Nakamura teaches the connecting step further comprises:

connecting each of the plurality of memory banks to one of a plurality of row address decoders, one of the plurality of row address decoders being connected to the processor (e.g., see Figure 2 and paragraphs 0056-0060); and,

connecting each of the plurality of memory banks to one of a plurality of column address decoders, one of the plurality of column address decoders being connected to the processor (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 51, Nakamura teaches simultaneously accessing step further comprises at least one of:

simultaneously exchanging row address information between the processor and more than one of the plurality of row address decoders (e.g., see Figure 2 and paragraphs 0056-0060);

simultaneously exchanging column address information between the processor and more than one of the plurality of column address decoders (e.g., see Figure 2 and paragraphs 0056-0060); and,

simultaneously exchanging data between the processor and more than one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060).

16. Nakamura teaches the invention (claim 52) as claimed including a method for increasing the throughput of an integrated circuit having a processor and a transparent SDRAM array, the transparent SDRAM array having a controller, a data bus and a plurality of memory banks, each of the plurality of memory banks being independently connected to the controller, the method comprising at least one of:

simultaneously reading data from more than one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060); and,

simultaneously writing data from more than one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060). The embedded SDRAM teaches the transparent memory array as a memory array which has a refresh operation for maintaining data in a power

down mode without input from a programmer or system designer. The refresh operation is performed using a refresh address counter without supplying the address to the address buffer of the memory array for each cell of the array (e.g., see Figures 6-7 and paragraphs 0069-0077).

As to claim 53, Nakamura teaches the simultaneously reading step further comprises: simultaneously exchanging read address information between the processor and more than one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060); and, providing a data signal from the plurality of memory banks to the data bus (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 54, Nakamura teaches the simultaneously writing step further comprises: simultaneously exchanging write address information between the processor and more than one of the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060); and, providing a data signal from the plurality of memory banks to the data bus (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 55, Nakamura teaches each of the memory banks has a row address decoder and a column address decoder associated therewith, the exchanging read address information step further comprises:

transmitting a first row address information from the processor to a first row address decoder (e.g., see Figure 2 and paragraphs 0056-0060);  
transmitting a first column address information from the processor to a first column address decoder (e.g., see Figure 2 and paragraphs 0056-0060); and,

simultaneously transmitting at least one of another row address information and column address information from the processor to at least one of another row address decoder and another column address decoder (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 56, Nakamura teaches providing a data signal from the plurality of memory banks to the data bus further comprises:

simultaneously decoding the read address information exchanged between the processor and more than one of the memory banks (e.g., see Figure 2 and paragraphs 0056-0060);  
selecting a memory cell within each of the memory banks based on the read address information (e.g., see Figure 2 and paragraphs 0056-0060); and,

simultaneously read the data signal from the selected memory cells within the plurality of memory banks (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 57, Nakamura teaches each of the memory banks has a row address decoder and a column address decoder associated therewith, the exchanging write address information step further comprises:

transmitting a first row address information from the processor to a first row address decoder (e.g., see Figure 2 and paragraphs 0056-0060);

transmitting a first column address information from the processor to a first column address decoder (e.g., see Figure 2 and paragraphs 0056-0060); and,

simultaneously transmitting at least one of another row address information and column address information from the processor to at least one of another row address decoder and another column address decoder (e.g., see Figure 2 and paragraphs 0056-0060).

As to claim 58, Nakamura teaches providing a data signal from the plurality of memory banks to the data bus further comprises:

simultaneously decoding the write address information exchanged between the processor and more than one of the memory banks (e.g., see Figure 1 and paragraph 0053);

selecting a memory cell within each of the memory banks based on the write address information (e.g., see Figure 1 and paragraph 0053); and,

simultaneously writing the data signal from the selected memory cells within the plurality of memory banks (e.g., see Figure 1 and paragraph 0053).

### ***RESPONSE TO APPLICANT'S REMARKS***

17. Applicant's arguments filed March 23, 2005 have been fully considered but they are not persuasive.

18. As to the misconstruction of the teachings of Nakamura, the actual use of the SDRAM of the reference is not pertinent to the application of the prior art.

19. Independent claims requiring a processor directly connected to a plurality of memory banks is taught by the reference. The memory array must function without either a precharge signal, a row address latch signal or a column address latch signal as the claim language uses the alternative language of '*without at least one of ...*', not all three of these conditions are required. The reference teaches an automatic refresh operation for the SDRAM in the power down mode using a counter without requiring a row address or a column address.

20. As to independent claims requiring '*a plurality of controllers.. each of the plurality of controllers being independently connected to the processor*', this limitation is taught to the extent required by the actual claim language. Each memory bank of Figure 2 has a command latch, a

controller and a selector connected in parallel to the command decoder, refresh address counter, address buffer and I/O buffer.

21. As to the memory banks not being independently connected to the processor, this limitation is also taught as the normal access mode of the memory is accessed in a random access fashion and does not require paging through the entire set of SDRAM blocks to access a particular memory location within the memory array. As to the reference not teaching a plurality of SDRAM arrays, the reference shows a plurality of memory banks and each memory bank comprises rows and columns which teaches the plurality of memory arrays to the extent required by the actual claim language.

#### ***ACTION FINALITY***

22. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

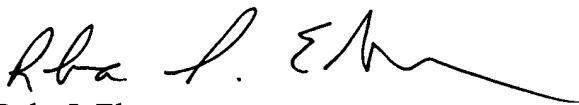
A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

### **CONCLUSION**

23. The prior art made of record, given on PTO form 892, and not relied upon is considered pertinent to applicant's disclosure. These references discuss aspects of auto-refresh operations.
24. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Reba I. Elmore, whose telephone number is (571) 272-4192. The examiner can normally be reached on M-TH from 7:30am to 6:00pm, EST.

If attempts to reach the examiner by telephone are unsuccessful, the art unit supervisor for AU 2187, Donald Sparks, can be reached for general questions concerning this application at (571) 272-4201. Additionally, the official fax phone number for the art unit is (703) 746-7239.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Tech Center central telephone number is (571) 272-2100.



Reba I. Elmore  
Primary Patent Examiner  
Art Unit 2187

May 10, 2005